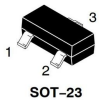
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Si2319DDS-T1-GE3
P-Channel 40 V (D-S) MOSFET

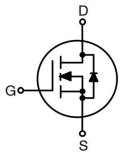
APPLICATIONS
- Battery switch
- Motor drive control
- Load switch

FEATURES
- TrenchFET® Gen III p-channel power MOSFET
- 100 % R_g and UIS tested



SOT-23

1 – Gate
2 – Source
3 – Drain



PRODUCT SUMMARY	
V_{DS} (V)	-40
$R_{DS(on)}$ max. (Ω) at V_{GS} = 10 V	0.075
$R_{DS(on)}$ max. (Ω) at V_{GS} = 4.5 V	0.100
Q_g typ. (nC)	6
I_D (A)	-3.6 [a]
Configuration	Single

ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and halogen-free	Si2319DDS-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	-40	V
Gate-source voltage		V_{GS}	± 20	
Continuous drain current (T_J = 150 °C)	T_C = 25 °C	I_D	-3.6	A
	T_C = 70 °C		-2.9	
	T_A = 25 °C		-2.7 [b, c]	
	T_A = 70 °C		-2.2 [b, c]	
Pulsed drain current (t = 100 µs)		I_{DM}	-15	
Continuous source-drain diode current	T_C = 25 °C	I_S	-1.4	
	T_A = 25 °C		-0.8 [b, c]	
Single pulse avalanche current	L = 0.1 mH	I_{AS}	-5	
Single pulse avalanche energy		E_{AS}	1.25	mJ
Maximum power dissipation	T_C = 25 °C	I_P	1.7	W
	T_C = 70 °C		1.1	
	T_A = 25 °C		1 [b, c]	
	T_A = 70 °C		0.6 [b, c]	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +150	°C

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient [b]	t ≤ 5 s	R_{thJA}	100	130	°C/W
Maximum junction-to-case (drain)	Steady state	R_{thJF}	60	75	

Notes
a. Based on T_C = 25 °C
b. Surface mounted on 1" x 1" FR4 board
c. t = 5 s
d. Maximum under steady state conditions is 175 °C/W

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SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = -250 µA	-40	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	I_D = -250 µA	-	-27.5	-	mV/°C
$V_{GS(th)}$ temperature coefficient	$\Delta V_{GS(th)}/T_J$	I_D = -250 µA	-	3.2	-	
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	-1	-	-2.5	V
Gate-source leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	-	-	100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} = -40 V, V_{GS} = 0 V	-	-	-1	µA
		V_{DS} = -40 V, V_{GS} = 0 V, T_J = 70 °C	-	-	-15	
On-state drain current [a]	$I_{D(on)}$	$V_{DS} \geq$ -10 V, V_{GS} = -10 V	-10	-	-	A
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} = -10 V, I_D = -2.7 A	-	0.062	0.075	Ω
		V_{GS} = -4.5 V, I_D = -2.4 A	-	0.081	0.100	
Forward transconductance [a]	g_{fs}	V_{DS} = -15 V, I_D = -2.7 A	-	10	-	S
Dynamic [b]						
Input capacitance	C_{iss}	V_{DS} = -20 V, V_{GS} = 0 V, f = 1 MHz	-	650	-	pF
Output capacitance	C_{oss}		-	54	-	
Reverse transfer capacitance	C_{rss}		-	43	-	
Total gate charge	Q_g	V_{DS} = -20 V, V_{GS} = -10 V, I_D = -2.7 A	-	12.5	19	nC
		V_{DS} = -20 V, V_{GS} = -4.5 V, I_D =-2.7 A	-	6	12	
Gate-source charge	Q_{gs}		-	1.8	-	
Gate-drain charge	Q_{gd}		-	2	-	
Gate resistance	R_g	f = 1 MHz	2	10	20	Ω
Turn-on delay time	$t_{d(on)}$	V_{DD} = -20 V, R_L = 9.1 Ω, $I_D \cong$ -2.2 A, V_{GEN} = -10 V, R_g = 1 Ω	-	10	20	ns
Rise time	t_r		-	20	30	
Turn-off delay time	$t_{d(off)}$		-	20	30	
Fall time	t_f		-	12	24	
Turn-on delay time	$t_{d(on)}$	V_{DD} = -20 V, R_L = 9.1 Ω, $I_D \cong$ -2.2 A, V_{GEN} = -4.5 V, R_g = 1 Ω	-	30	45	
Rise time	t_r		-	32	48	
Turn-off delay time	$t_{d(off)}$		-	20	30	
Fall time	t_f		-	15	30	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	T_C = 25 °C	-	-	-1.4	A
Pulse diode forward current	I_{SM}		-	-	-15	
Body diode voltage	V_{SD}	I_S = -2.2 A, V_{GS} = 0 V	-	-0.8	-1.2	V
Body diode reverse recovery time	t_{rr}	I_F = -2.2 A, di/dt = 100 A/µs, T_J = 25 °C	-	15	30	ns
Body diode reverse recovery charge	Q_{rr}		-	9	18	nC
Reverse recovery fall time	t_a		-	10.5	-	ns
Reverse recovery rise time	t_b		-	4.5	-	

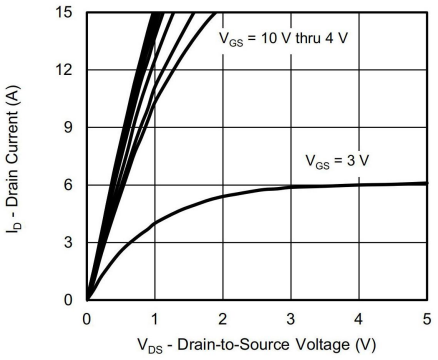
Notes

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %

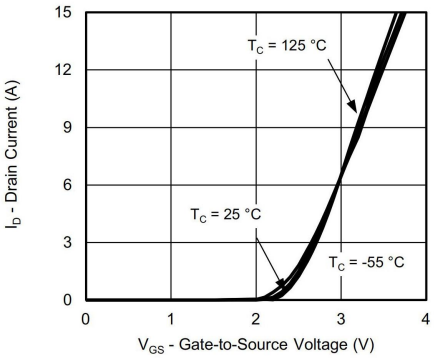
b. Guaranteed by design, not subject to production testing

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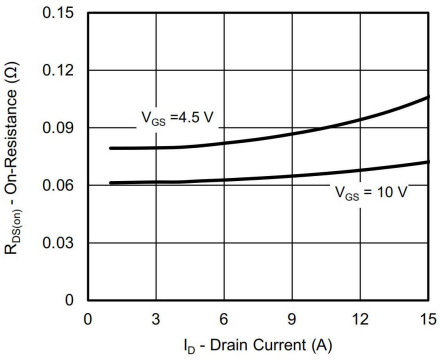
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



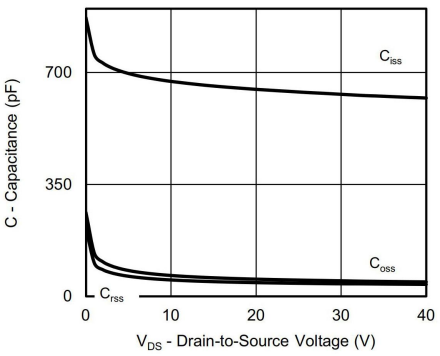
Output Characteristics



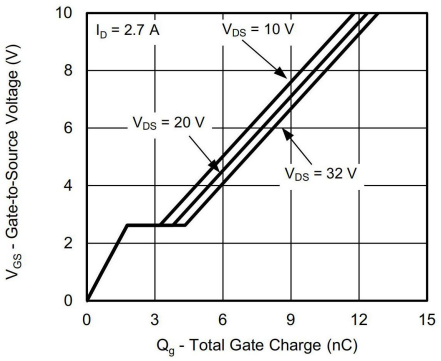
Transfer Characteristics



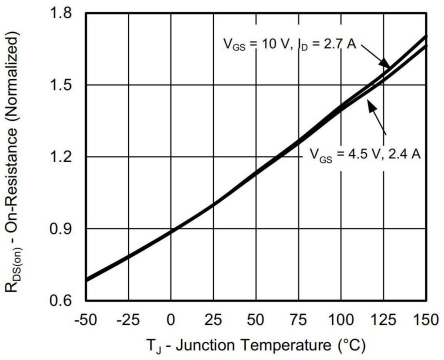
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



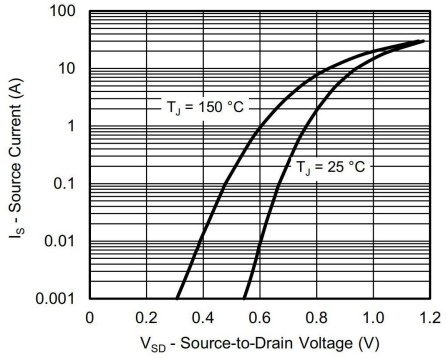
Gate Charge



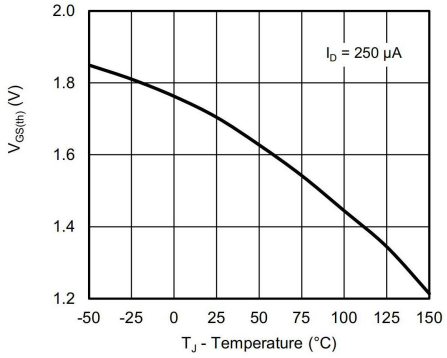
On-Resistance vs. Junction Temperature

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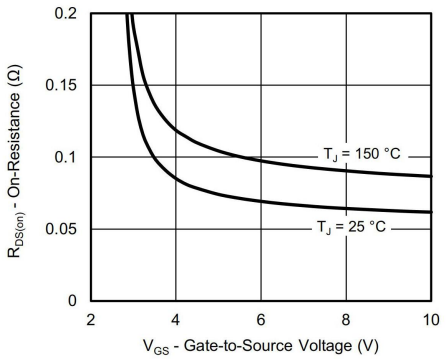
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



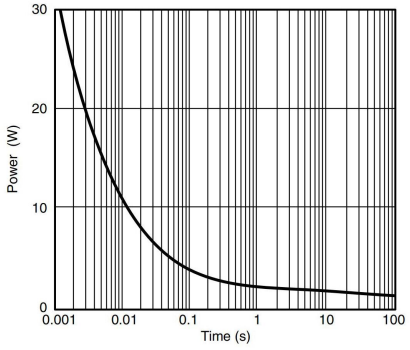
Source-Drain Diode Forward Voltage



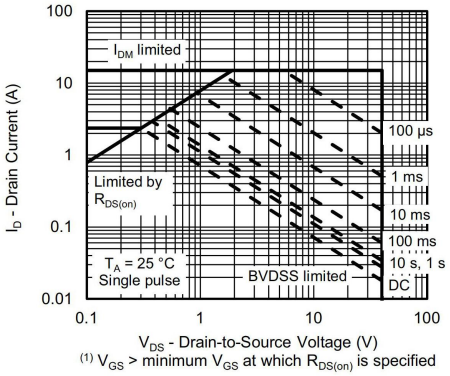
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient

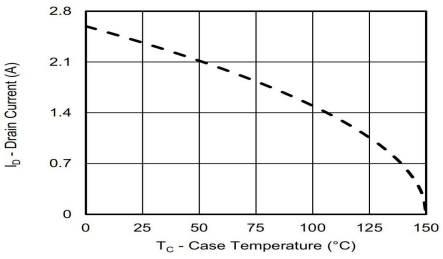


(1) V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

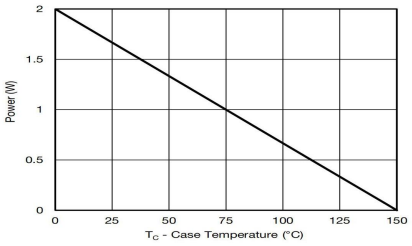
Safe Operating Area, Junction-to-Ambient

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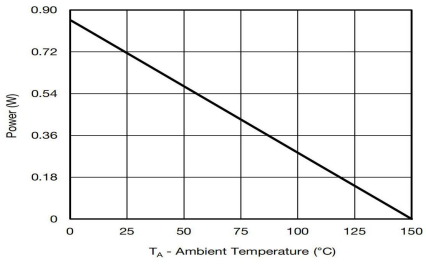
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating [a]



Power, Junction-to-Case

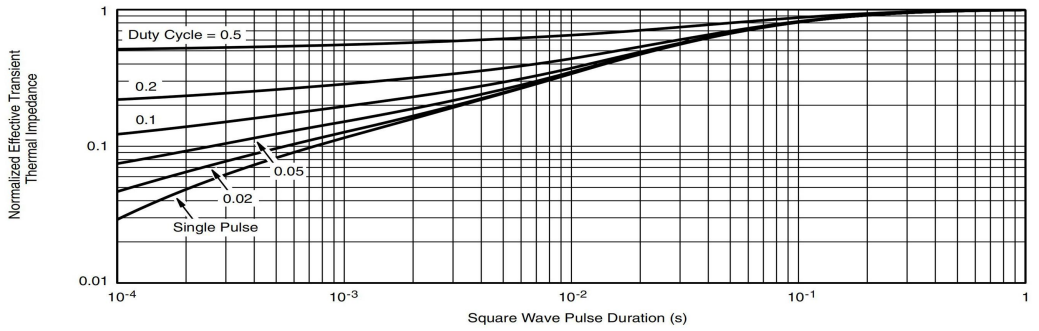


Power, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



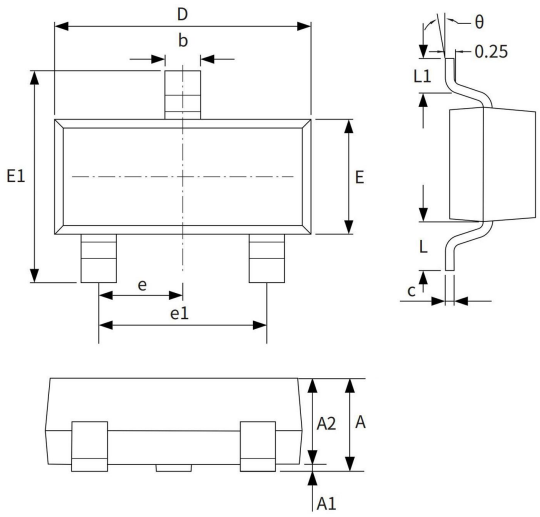
Normalized Thermal Transient Impedance, Junction-to-Case

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Ordering Information

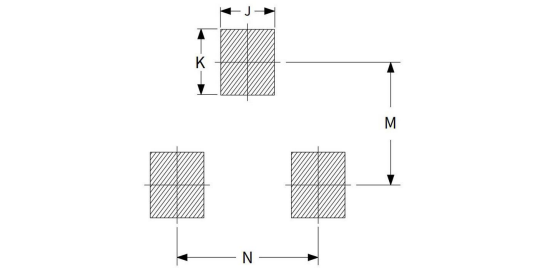
PACKAGE	PACKAGE CODE	UNIT WEIGHT(g)	REEL(pcs)	BOX(pcs)	CARTON(pcs)	DELIVERY MODE
SOT-23	R1	0.008	3000	30000	240000	7''

Package Outline Dimensions (SOT-23)



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.90	1.15	0.035	0.045
A1	-	0.10	-	0.004
A2	0.90	1.05	0.035	0.041
b	0.30	0.50	0.012	0.020
c	0.10	0.20	0.004	0.008
D	2.80	3.00	0.110	0.118
E	1.20	1.40	0.047	0.055
E1	2.25	2.55	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.80	2.00	0.071	0.079
L	0.550REF		0.022REF	
L1	0.30	0.50	0.012	0.020
θ	-	8°	-	8°

Suggested Pad Layout



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
J	0.75	0.85	0.030	0.033
K	0.85	0.95	0.033	0.037
M	1.95	2.05	0.077	0.081
N	1.85	1.95	0.073	0.077